

## ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

**Title of  
Invention**

High fT and fmax Bipolar Transistor and Method of Making  
Same

Application Number:

Confirmation Number:

First Named Applicant: Alvin Joseph

Attorney Docket Number: BUR920030004US1

Search string: ( 6333236 or 6262472 or 6028345 or 5962880 or 5624856 or 5436180 or  
4752817 or 20020058388 ).pn.

### US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	6333236	2001-12-25	Koganei		438	312
	2	6262472	2001-07-17	Gregory		257	592
	3	6028345	2000-02-22	Johnson		257	592
	4	5962880	1999-10-05	Oda et al.		257	198
	5	5624856	1997-04-29	Li et al.		438	339
	6	5436180	1995-07-25	de Fresart et al.		437	31
	7	4752817	1988-06-21	Lechaton et al.		357	34

### US Published Applications

Note: Applicant is not required to submit a paper copy of cited US Published Applications

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
	1	20020058388	2002-05-16	Ryum et al.		438	364

**Signature**

<b>Examiner Name</b>	<b>Date</b>